

**Abstract****Epitaxially coated semiconductor wafer of monocrystalline silicon and method for the production thereof**

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A semiconductor wafer of monocrystalline silicon having a diameter of not less than 300 mm and method of producing a coated semiconductor wafer of monocrystalline silicon. The semiconductor wafer comprises a substrate wafer of monocrystalline silicon and a dopant-containing epitaxial layer of monocrystalline silicon atop the

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substrate wafer, wherein an inhomogeneity of the thickness of the epitaxial layer is not more than 0.5% and an inhomogeneity of the specific electrical resistance of the epitaxial layer is not more than 2%.

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Drawing relating to abstract: fig. 8